Silicon N-Channel MOS FET

HITACHI

ADE-208-1299 (Z) 1st. Edition Mar. 2001

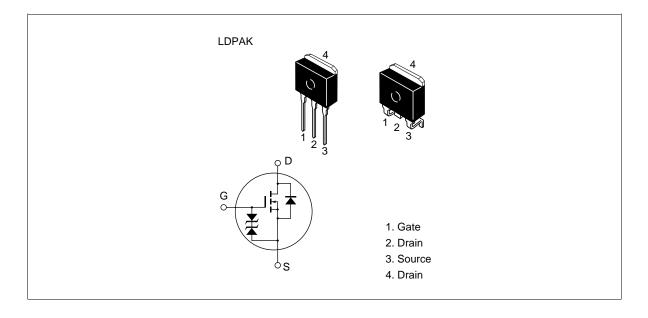
Application

High speed power switching

Features

- Low on-resistance
- · High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Drain to source voltage	$V_{(BR)DSS}$	100	V	
Gate to source voltage	$V_{\sf GSS}$	±20	V	
Drain current	I _D	20	Α	
Drain peak current	I _{D(pulse)} *1	80	А	
Body to drain diode reverse drain current	I _{DR}	20	Α	
Channel dissipation	Pch*2	50	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes 1. PW 10 µs, duty cycle 1%

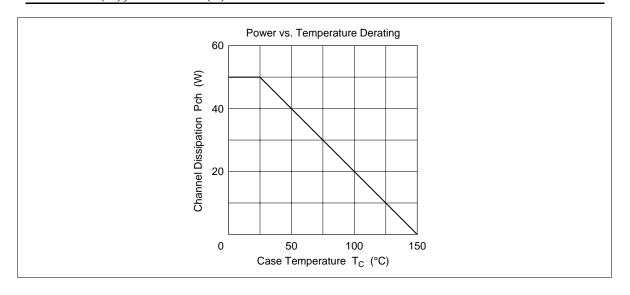
2. Value at $T_c = 25$ °C

Electrical Characteristics ($Ta = 25^{\circ}C$)

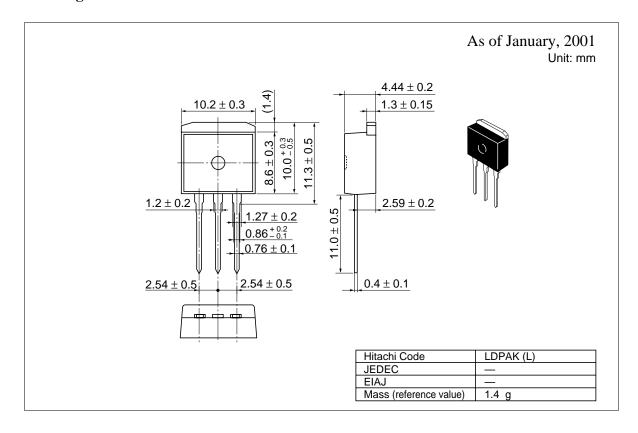
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 80 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static Drain to source on state	$R_{\scriptscriptstyle DS(on)}$	_	0.065	0.085		$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$	
resistance		_	0.085	0.12		$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$	
Forward transfer admittance	yfs	10	16	_	S	$I_{D} = 10 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$	
Input capacitance	Ciss	_	1300	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	_	540	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	_	160	_	pF		
Turn-on delay time	$t_{d(on)}$	_	12	_	ns	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V},$	
Rise time	t _r	_	100	_	ns	$R_L = 3$	
Turn-off delay time	t _{d(off)}	_	300	_	ns	_	
Fall time	t _f	_	150	_	ns		
Body to drain diode forward voltage	V_{DF}	_	1.3	_	V	$I_F = 20 \text{ A}, V_{GS} = 0$	
Body to drain diode reverse recovery time	t _{rr}		300		ns	$I_F = 20 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A/}\mu\text{s}$	

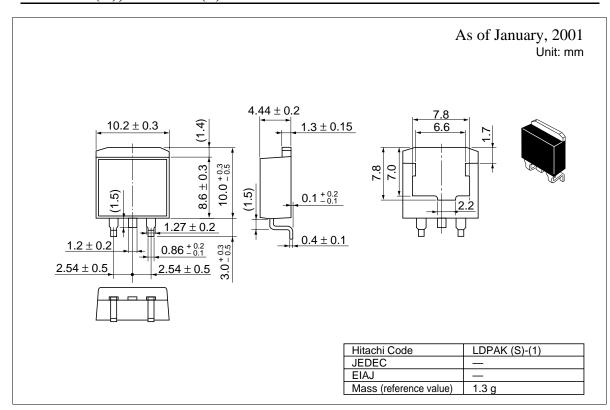
Note 1. Pulse test

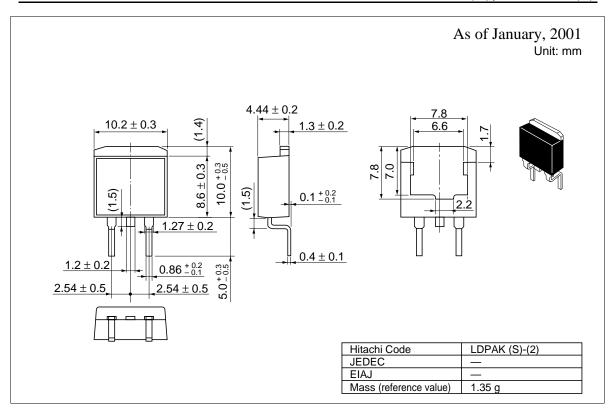
See characteristic curves of 2SK1302.



Package Dimensions







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